Product Summary

BV_{DSS}	$R_{DS(ON)\ MAX}$	Package	I_D T_A = +25°C
-20V	38mΩ @ V_{GS} = -10V	SOT23	-4.3A
	43mΩ @ V_{GS} = -4.5V		-4.0A
	75mΩ @ V_{GS} = -2.5V		-2.8A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- Power Management Functions

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Up To 3kV**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

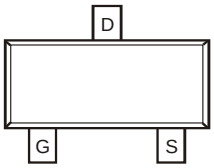
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

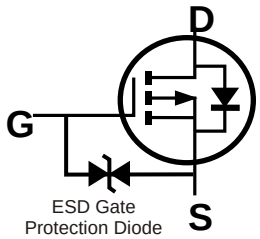
ESD PROTECTED TO 3kV

SOT23

Top View



Top View
Internal Schematic



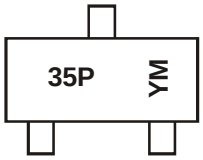
Equivalent Circuit
(Note 5)

Ordering Information (Notes 5 & 6)

Part Number	Compliance	Case	Packaging
DMP2100U-7	Standard	SOT23	3,000/Tape & Reel
DMP2100UQ-7	Automotive	SOT23	3,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Please refer to http://www.diodes.com/product_compliance_definitions.html.
5. The ESD gate protection diode is only designed to protect against ESD events. No gate-source voltage greater than the maximum V_{GSS} rating (given on page 2) can be applied.
6. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



35P = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: E = 2017)
M = Month (ex: 9 = September)

Date Code Key

Year	2008	~	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	V	~	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage (Note 7)			V_{GSS}	±10	V
Continuous Drain Current (Note 9) V_{GS} = -10V	Steady State	T_A = +25°C T_A = +70°C	I_D	-4.3 -3.4	A
	t<5s	T_A = +25°C T_A = +70°C	I_D	-5.5 -4.3	A
Maximum Continuous Body Diodes Forward Current (Note 9)			I_S	-2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-30	A
Pulsed Body Diodes Forward Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	-30	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 8)	T_A = +25°C	P_D	0.8	W
	T_A = +70°C		0.5	
Thermal Resistance, Junction to Ambient (Note 8)	Steady State	$R_{\theta JA}$	161	°C/W
	t<5s		96	
Total Power Dissipation (Note 9)	T_A = +25°C	P_D	1.3	W
	T_A = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 9)	Steady State	$R_{\theta JA}$	99	°C/W
	t<5s		60	
Thermal Resistance, Junction to Case (Note 9)		$R_{\theta JC}$	15	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 10)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 10)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.3	—	-1.4	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	25	38	mΩ	V_{GS} = -10V, I_D = -3.5A
		—	29	43		V_{GS} = -4.5V, I_D = -3A
		—	37	75		V_{GS} = -2.5V, I_D = -1A
		—	47	—		V_{GS} = -1.8V, I_D = -0.5A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	3	—	S	V_{DS} = -5V, I_D = -4A
DYNAMIC CHARACTERISTICS (Note 11)						
Input Capacitance	C_{iss}	—	216	—	pF	V_{DS} = -15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	90	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	24	—	pF	
Gate Resistnace	R_g	—	250	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 11)						
Total Gate Charge	Q_g	—	9.1	—	nC	V_{GS} = -4.5V, V_{DS} = -10V I_D = -4A
Gate-Source Charge	Q_{gs}	—	1.6	—	nC	
Gate-Drain Charge	Q_{gd}	—	2.0	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	80	—	ns	V_{DS} = -10V, V_{GS} = -4.5V, R_D = 2.5Ω, R_G = 3.0Ω
Turn-On Rise Time	t_R	—	155	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	688	—	ns	
Turn-Off Fall Time	t_F	—	423	—	ns	

Notes:
7. AEC-Q101 V_{GS} maximum is ±9.6V.
8. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
9. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
10. Short duration pulse test used to minimize self-heating effect.
11. Guaranteed by design. Not subject to product testing.

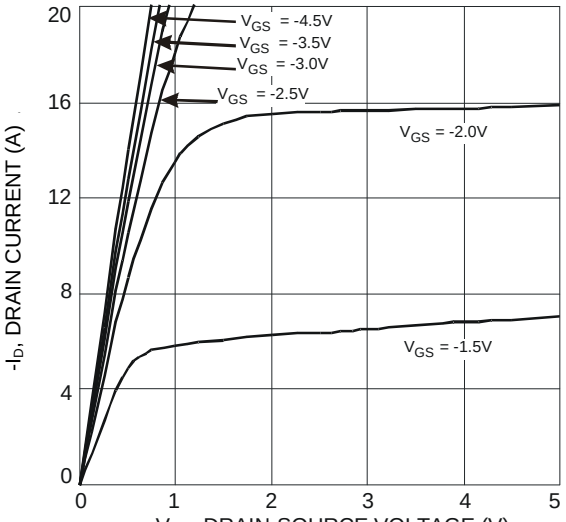


Fig. 1 Typical Output Characteristic

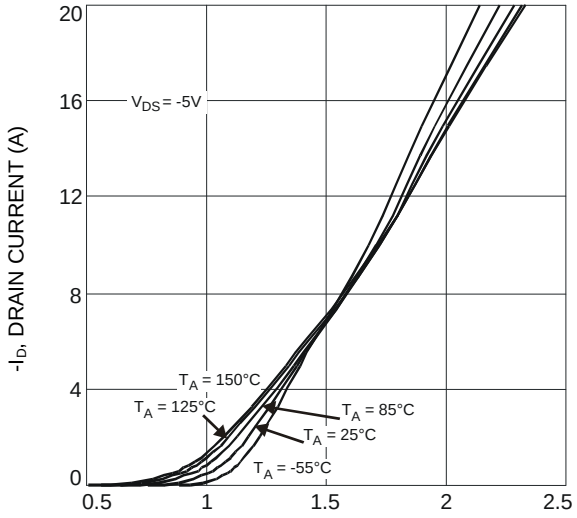


Fig. 2 Typical Transfer Characteristic

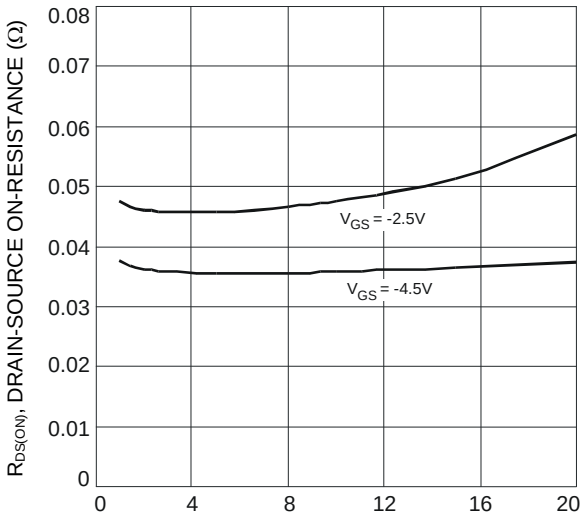


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

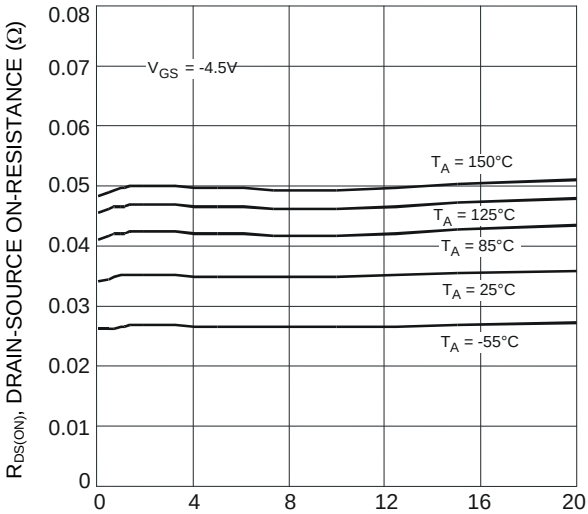


Fig. 4 Typical On-Resistance
vs. Drain Current and Temperature

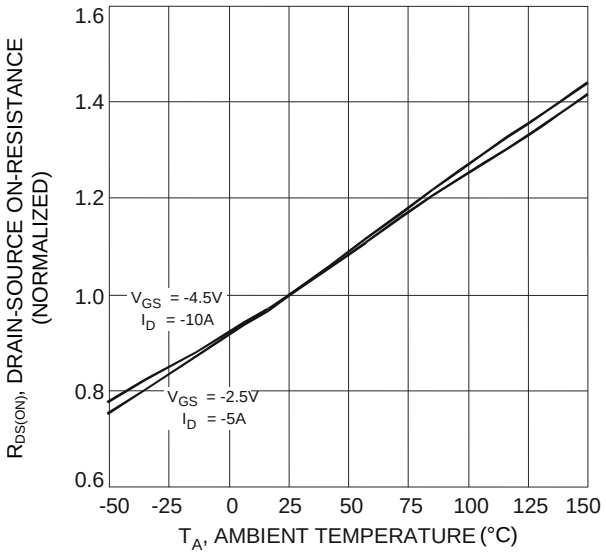


Fig. 5 On-Resistance Variation with Temperature

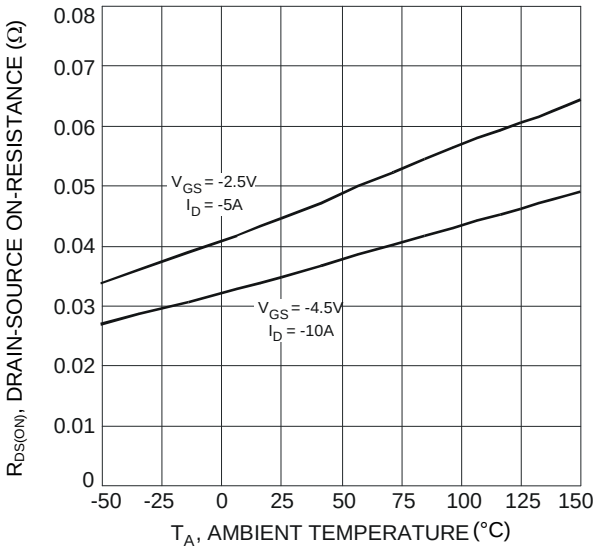


Fig. 6 On-Resistance Variation with Temperature

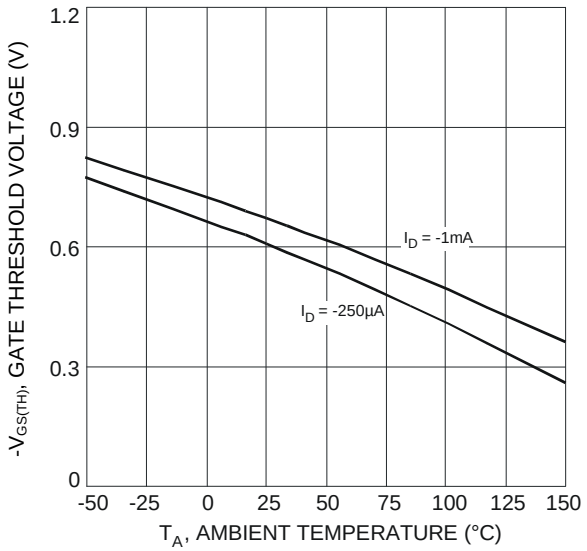


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

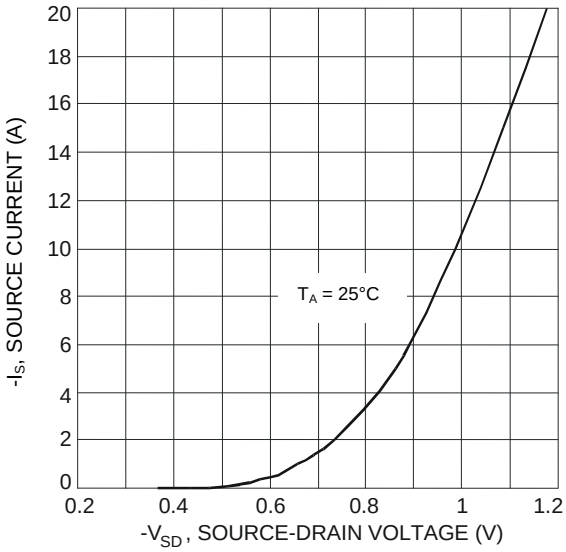


Fig. 8 Diode Forward Voltage vs. Current

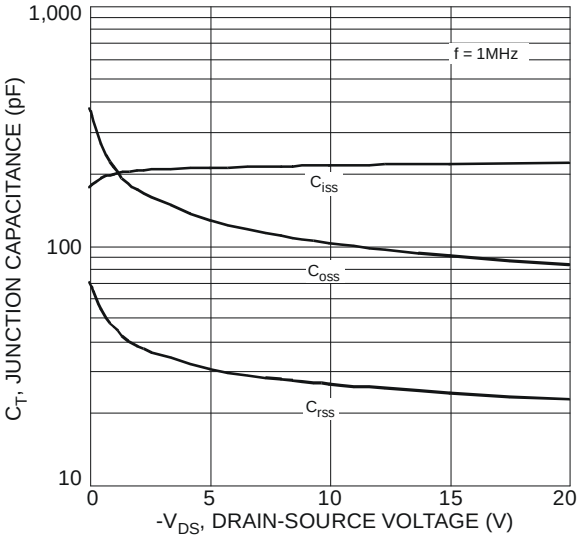


Fig. 9 Typical Junction Capacitance

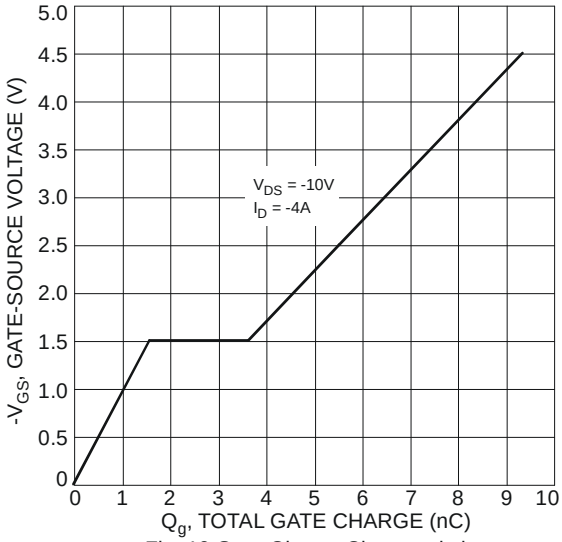


Fig. 10 Gate-Charge Characteristics

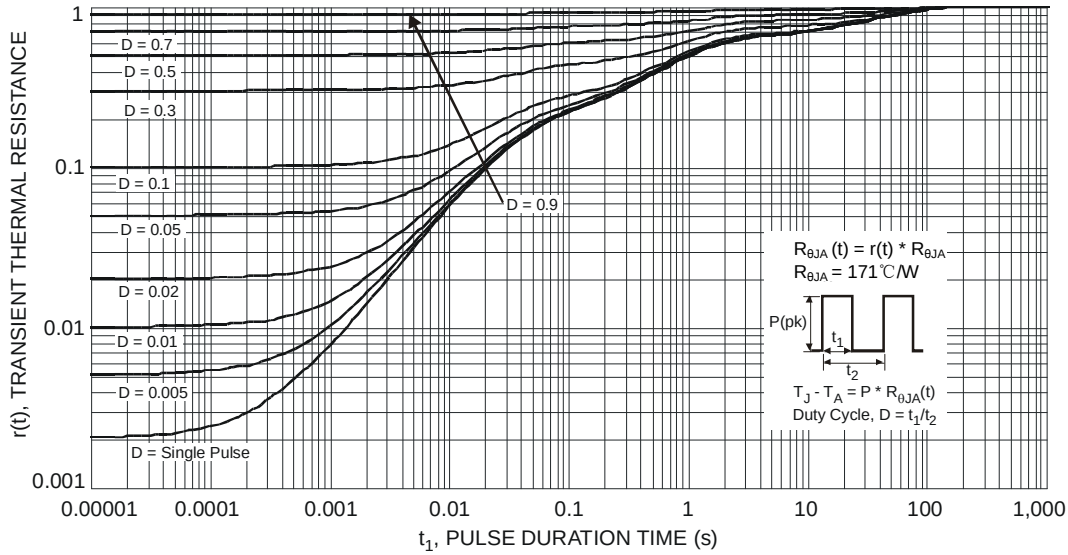
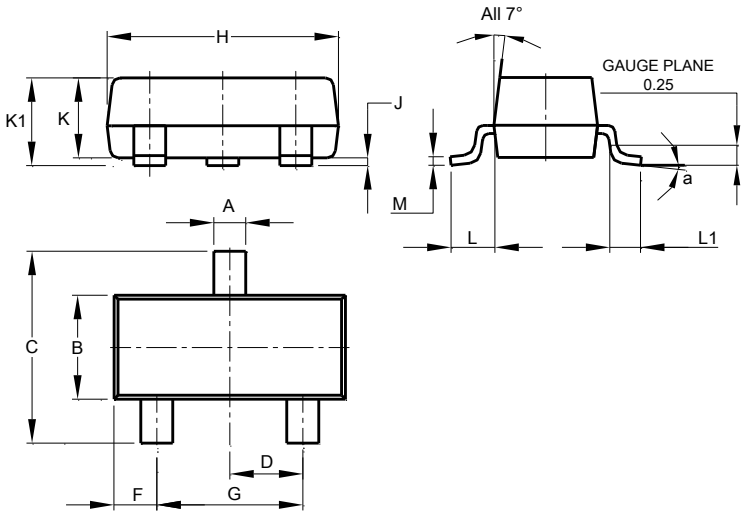


Fig. 11 Transient Thermal Response

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

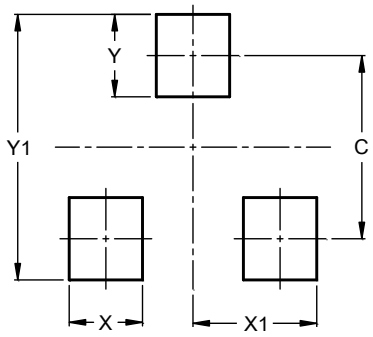


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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